

isc Silicon NPN Power Transistor

2SC2073

DESCRIPTION

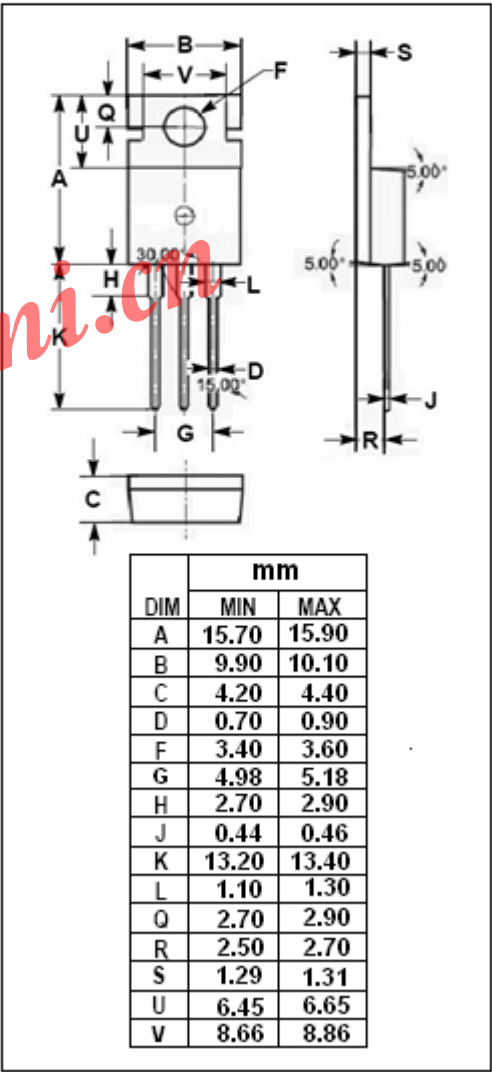
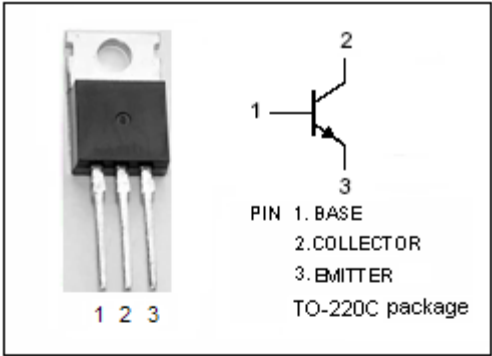
- Collector-Emitter Breakdown Voltage-
:V_{(BR)CEO}= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940

APPLICATIONS

- Power amplifier applications.
- Vertical output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	150	V
V _{CEO}	Collector-Emitter Voltage	150	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	1.5	A
I _B	Base Current-Continuous	0.5	A
P _C	Collector Power Dissipation @ T _a =25°C	1.5	W
	Collector Power Dissipation @ T _c =25°C	25	
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



ISC Silicon NPN Power Transistor**2SC2073****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 500mA ; V _{CE} = 10V			0.85	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V ; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 500mA ; V _{CE} = 10V	40		140	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		35		pF
f _T	Current-Gain—Bandwidth Product	I _C = 500mA; V _{CE} = 10V		4		MHz

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